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(54) **FILM FORMING DEVICE**

(57) The present invention has an object to provide a film forming apparatus that can form a thin film on a substrate and can enhance throughput of film forming treatment, without reducing film forming quality and a film forming rate. In the present invention, a heating chamber (H10) and a film forming chamber (F10) are disposed along a substrate conveyance path circle (M1). The heating chamber (H10) and the film forming chamber (F10) are disposed adjacently to each other. With a substrate conveying apparatus (8), a plurality of substrates (10) are simultaneously conveyed along the substrate conveyance path circle (M1), with a substrate rotation direction (R1) being a moving direction. After heating treatment of infrared radiation apparatuses (2, 4) in the heating chamber (H10) is performed for the substrates (10), mist spraying treatment of thin film forming nozzles (1L, 1H) in the film forming chamber (F10) is performed for the substrates (10). In this manner, a thin film is formed on each of a front surface and a back surface of the plu-

rality of substrates (10).

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